

**SIXTH SEMESTER B.TECH. (E & C) DEGREE END SEMESTER EXAMINATION****JUNE 2019****SUBJECT: INTRODUCTION TO NANOSCIENCE AND TECHNOLOGY (ECE - 3290)****TIME: 3 HOURS****MAX. MARKS: 50****Instructions to candidates**

- Answer **ALL** questions.
- Missing data may be suitably assumed.

- 1A. Explain how the FCC and HCP structures can be called as close packed structures.
- 1B. Calculate number of atoms in a 1.4 nm diameter of Pt. Consider that Pt has FCC structure with the lattice parameter 0.391 Å.
- 1C. What is Hamiltonian? Write the law of conservation of energy in terms of Hamiltonian for a particle moving in a potential field which is independent of time. (4+3+3)
- 2A. Derive the time independent Schrodinger equation and explain its importance.
- 2B. Explain an experiment that proves that the matter waves indeed exhibit the interference phenomenon.
- 2C. Describe the nature of the solution for a particle confined in a classically allowed region under an arbitrary potential well. How it differs with that in the classically forbidden region. (4+3+3)
- 3A. Determine the energy density of a progressing plane wave and also the standing waves. Comment on the result.
- 3B. Indicate the energy and the wave functions of first four energy levels of a particle confined in a potential well having infinite potential walls.
- 3C. Define the phase velocity of a wave. Taking an example to define the eigen function and associated eigen value. (4+3+3)
- 4A. Describe experimental techniques to grow the CNT by utilising the catalyst nanostructures.
- 4B. Write the chemical equations in preparation of electronic grade Si.
- 4C. Explain the photolithography process and explain its limitation. Indicate the ways and means to circumvent this problem. (4+3+3)
- 5A. Explain the principle of AFM and how it differs with that of STM. Explain with an example how STM can be utilised to manipulate the atoms on a surface.
- 5B. Explain the principles of the SEM and TEM. Explain how to prepare a sample for TEM study.
- 5C. Explain the experimental procedure for STM tips preparation. (4+3+3)